



《风光欣》技术资料

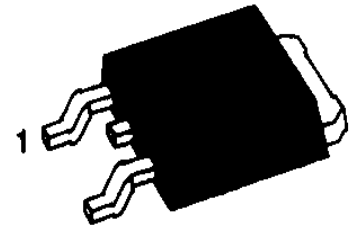
2SD1802

NPN EPITAXIAL SILICON TRANSISTOR

*Complement to 2SB1202

ABSOLUTE MAXIMUM RATINGS(Ta=25)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CBO}	60	V
Collector-Emitter Voltage	V _{CEO}	50	V
Emitter -Base Voltage	V _{EBO}	6	V
Collector Current (DC)	I _c	3	A
Collector Current (Pulse)	I _{cp}	6	A
Collector Dissipation	P _c	1	W
Junction Temperature	T _J	150	
Storage Temperature	T _{STG}	-55 ~150	



SOT-252

1.Base 2.Collector 3.Emitter

ELECTRICAL CHARACTERISTICS(Ta=25)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Cutoff Current	I _{CBO}	V _{CB} = 40V,I _E =0			1	μ A
Emitter-Cutoff Current	I _{EBO}	V _{EB} = 4V,I _C =0			1	μ A
*DC Current Gain	h _{FE1}	V _{CE} = 2V,I _c = 100mA	100		560	
	h _{FE2}	V _{CE} = 2V,I _c = 4A	35			
Current Gain-Bandwidth Product	f _T	V _{CE} = 10V,I _C =50mA		150		MHZ
Output Capacitance	C _{OB}	V _{CB} = 10V,I _E =0,f=1MHZ		25		pF
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _c = 2A,I _B = 100mA		190	500	mV
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _c = 2A,I _B = 100mA		0.95	1.2	V
Collector-to-Base Breakdown Voltage	V _{BR(CBO)}	I _c = 10 μ A,I _E = 0	60			V
Collector-to-Emitter Breakdown Voltage	V _{BR(CEO)}	I _c = 1mA,R _{BE} =	50			V
Emitter-to-Base Breakdown Voltage	V _{BR(EBO)}	I _E = 10 μ A,I _C = 0	6			V
Turn-ON Time	t _{ON}	See specified Test Circuit		70		ns
Storage Time	t _{stg}	See specified Test Circuit		650		ns
Fall Time	t _f	See specified Test Circuit		35		ns

H_{FE} (2) CLASSIFICATION

Classification	Q	R	S	T
H _{FE} (2)	70-140	100-200	140-280	200-400